

**HI-508/883**

Single 8-Channel CMOS Analog Multiplexer

FN8290  
Rev.0.00  
May 3, 2012

The HI-508/883 is an eight channel single-ended multiplexer. This monolithic CMOS multiplexer includes an array of eight analog switches, a digital decode circuit for channel selection, a voltage reference for logic thresholds, and an ENABLE input for device selection when several multiplexers are present.

The Dielectric Isolation (DI) process used in fabrication of this device eliminates the problem of latch-up. Also, DI offers much lower substrate leakage and parasitic capacitance than conventional junction-isolated CMOS. Switches are guaranteed to break-before-make, so that two channels are never shorted together. The switching threshold for each digital input is established by an internal +5V reference, providing a guaranteed minimum 2.4V for logic "1" and Maximum 0.8V for logic "0". This allows direct interface without pull-up resistors to signals from most logic families: CMOS, TTL, DTL and some PMOS. For protection against transient overvoltage, the digital inputs include a series 200Ω resistor and a diode clamp to each supply. If input overvoltage protection is needed, the HI-548/883 and HI-549/883 multiplexers are recommended. For further information see Application Note [AN520](#).

**Features**

- This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- Low On Resistance (Max)..... 400Ω
- Wide Analog Signal Range ..... ±15V
- TTL/CMOS Compatible ..... 2.4V (Logic "1")
- Access Time (Max) ..... 1.0μs
- 44V Maximum Power Supply
- Break-Before-Make Switching
- No Latch-up

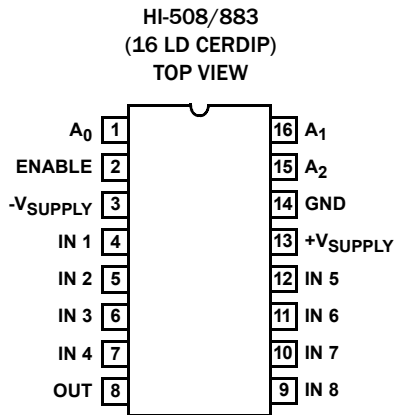
**Applications**

- Data Acquisition Systems
- Precision Instrumentation
- Demultiplexing
- Selector Switch

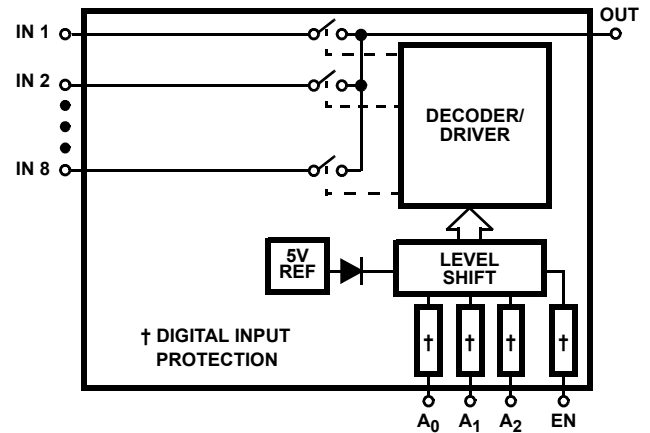
**Ordering Information**

PART #	PART MARKING	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #
HI1-0508/883	HI1-508/883	-55 to 125	16 Ld CerDIP	F16.3

**Pin Configuration**



**Functional Diagram**



TRUTH TABLE HI-508/883

A <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>	EN	"ON" CHANNEL
X	X	X	L	None
L	L	L	H	1
L	L	H	H	2
L	H	L	H	3
L	H	H	H	4
H	L	L	H	5
H	L	H	H	6
H	H	L	H	7
H	H	H	H	8

### Absolute Maximum Ratings

Voltage Between Supply Pins .....	44V
+V <sub>SUPPLY</sub> to Ground .....	22V
-V <sub>SUPPLY</sub> to Ground .....	22V
Analog Input Voltage, +V <sub>S</sub> .....	+V <sub>SUPPLY</sub> +2V
-V <sub>S</sub> .....	-V <sub>SUPPLY</sub> -2V
Digital Input Voltage, +V <sub>EN</sub> , +V <sub>A</sub> .....	+V <sub>SUPPLY</sub> +4V
-V <sub>EN</sub> , -V <sub>A</sub> .....	-V <sub>SUPPLY</sub> +4V
	or 20mA, whichever occurs first
Continuous Current, S or D .....	20mA
Peak Current, S or D (Pulsed at 1ms, 10% Duty Cycle Max) .....	40mA
ESD Classification .....	≤2000V

### Thermal Information

Thermal Resistance	$\theta_{JA}$ (°C/W)	$\theta_{JC}$ (°C/W)
CerDIP Package .....	83	21
Power Dissipation (At +75°C)		
CerDIP Package .....	1.20W	
Power Dissipation Derating Factor (Above +75°C)		
CerDIP Package .....	.12.0mW/°C	
Junction Temperature .....	+175°C	
Storage Temperature Range .....	-65°C to +150°C	
Lead Temperature (Soldering 10s) .....	+275°C	

### Recommended Operating Conditions

Operating Temperature Range .....	-55°C to +125°C
Operating Supply Voltage ( $\pm V_{SUPPLY}$ ) .....	$\pm 15V$
Analog Input Voltage (V <sub>S</sub> ) .....	$\pm V_{SUPPLY}$
Logic Low Level (V <sub>AL</sub> ) .....	.0V to 0.8V
Logic High Level (V <sub>AH</sub> ) .....	2.4V to +V <sub>SUPPLY</sub>
Max RMS Current, S or D .....	8mA

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

**TABLE 1. D.C. ELECTRICAL PERFORMANCE SPECIFICATIONS**

Device Tested at: +V<sub>SUPPLY</sub> = +15V, -V<sub>SUPPLY</sub> = -15V, V<sub>EN</sub> = 2.4V, unless otherwise specified.

D.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE (°C)	MIN	MAX	UNITS
Input Leakage Current	I <sub>IH</sub>	Measure inputs sequentially, connect all unused inputs to GND	1, 2, 3	+25, +125, -55	-1.0	1.0	µA
	I <sub>IL</sub>		1, 2, 3	+25, +125, -55	-1.0	1.0	µA
Source "OFF" Leakage Current	+I <sub>S(OFF)</sub>	V <sub>S</sub> = +10V, V <sub>D</sub> = -10V, V <sub>EN</sub> = 0.8V, All unused inputs = -10V	1	+25	-10	10	nA
			2, 3	+125, -55	-50	50	nA
	-I <sub>S(OFF)</sub>	V <sub>S</sub> = -10V, V <sub>D</sub> = +10V, V <sub>EN</sub> = 0.8V, All unused inputs = +10V	1	+25	-10	10	nA
			2, 3	+125, -55	-50	50	nA
Drain "OFF" Leakage Current	+I <sub>D(OFF)</sub>	V <sub>D</sub> = +10V, V <sub>EN</sub> = 0.8V, All unused inputs = -10V	1	+25	-10	10	nA
			2, 3	+125, -55	-200	200	nA
	-I <sub>D(OFF)</sub>	V <sub>D</sub> = -10V, V <sub>EN</sub> = 0.8V, All unused inputs = +10V	1	+25	-10	10	nA
			2, 3	+25 to +125	-200	200	nA
Channel "ON" Leakage Current	+I <sub>D(ON)</sub>	V <sub>S</sub> = V <sub>D</sub> = +10V, All unused inputs = -10V	1	+25	-10	10	nA
			2, 3	+125, -55	-200	200	nA
	-I <sub>D(ON)</sub>	V <sub>S</sub> = V <sub>D</sub> = -10V, All unused inputs = +10V	1	+25	-10	10	nA
			2, 3	+125, -55	-200	200	nA
Positive Supply Current	+I	V <sub>A</sub> = 0V, V <sub>EN</sub> = 2.4V	1, 2, 3	+25, +125, -55	-	2.4	mA
Negative Supply Current	-I	V <sub>A</sub> = 0V, V <sub>EN</sub> = 2.4V	1, 2, 3	+25, +125, -55	-1.0	-	mA
Standby Positive Supply Current	+I <sub>SBY</sub>	V <sub>A</sub> = 0V, V <sub>EN</sub> = 0V	1, 2, 3	+25, +125, -55		2.4	mA
Standby Negative Supply Current	-I <sub>SBY</sub>	V <sub>A</sub> = 0V, V <sub>EN</sub> = 0V	1, 2, 3	+25, +125, -55	-1.0	-	mA
Switch "ON" Resistance	+R <sub>DS1</sub>	V <sub>S</sub> = 10V, I <sub>D</sub> = 1mA	1	+25	-	300	Ω
			2, 3	+125, -55	-	400	Ω
	-R <sub>DS1</sub>	V <sub>S</sub> = -10V, I <sub>D</sub> = -1mA	1	+25	-	300	Ω
			2, 3	+125, -55	-	400	Ω

**TABLE 1. D.C. ELECTRICAL PERFORMANCE SPECIFICATIONS (Continued)**

Device Tested at: +V<sub>SUPPLY</sub> = +15V, -V<sub>SUPPLY</sub> = -15V, V<sub>EN</sub> = 2.4V, unless otherwise specified.

D.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE (°C)	MIN	MAX	UNITS
Logic Level Voltage	V <sub>AL</sub>	Note 1	1, 2, 3	+25, +125	-	0.8	V
	V <sub>AH</sub>	Note 1	1, 2, 3	-55	2.4	-	V

**TABLE 2. A.C. ELECTRICAL PERFORMANCE SPECIFICATIONS**

Device Tested at: +V<sub>SUPPLY</sub> = +15V, -V<sub>SUPPLY</sub> = -15V, V<sub>EN</sub> = 2.4V, unless otherwise specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE (°C)	MIN	MAX	UNITS
Break-Before-Make Time Delay	t <sub>D</sub>	R <sub>L</sub> = 200Ω, C <sub>L</sub> = 12.5pF	9	+25	25		ns
Propagation Delay Times: Address Inputs to I/O Channel Times	t <sub>A</sub>	R <sub>L</sub> = 10MΩ, C <sub>L</sub> = 14pF	9	+25		500	ns
			10, 11	+125, -55		1000	ns
Enable to I/O	t <sub>ON(EN)</sub>	R <sub>L</sub> = 200Ω, C <sub>L</sub> = 12.5pF	9	+25		500	ns
			10, 11	+125, -55		1000	ns
	t <sub>OFF(EN)</sub>	R <sub>L</sub> = 200Ω, C <sub>L</sub> = 12.5pF	9	+25		500	ns
			10, 11	+125, -55		1000	ns

**TABLE 3. ELECTRICAL PERFORMANCE SPECIFICATIONS**

Device Tested at: +V<sub>SUPPLY</sub> = +15V, -V<sub>SUPPLY</sub> = -15V, V<sub>EN</sub> = 2.4V, unless otherwise specified.

PARAMETERS	SYMBOL	CONDITIONS	NOTE	TEMPERATURE (°C)	MIN	MAX	UNITS
Capacitance Address Input	C <sub>A</sub>	V+ = V- = 0V, f = 1MHz	2	+25		10	pF
Capacitance Output Switch	C <sub>OS</sub>	V+ = V- = 0V f = 1MHz	2	+25		45	pF
Capacitance Input Switch	C <sub>IS</sub>	V+ = V- = 0V, f = 1MHz	2	+25		12	pF
Charge Transfer Error	V <sub>CTE</sub>	V <sub>S</sub> = GND, V <sub>GEN</sub> = 0V to 5V	2	+25		10	mV
Off Isolation	V <sub>ISO</sub>	V <sub>EN</sub> = 0.8V, R <sub>L</sub> = 1kΩ, C <sub>L</sub> = 15pF, V <sub>S</sub> = 7V <sub>RMS</sub> , f = 100kHz	2, 3	+25	-50		dB

NOTES:

1. Used for forcing conditions for all DC Tests, unless otherwise specified.
2. The parameters listed in this table are controlled via design or process parameters and are not directly tested. These parameters are characterized upon initial design release and upon design changes which would affect these characteristics.
3. Worst case isolation occurs on channel 4 due to proximity of the output pins.

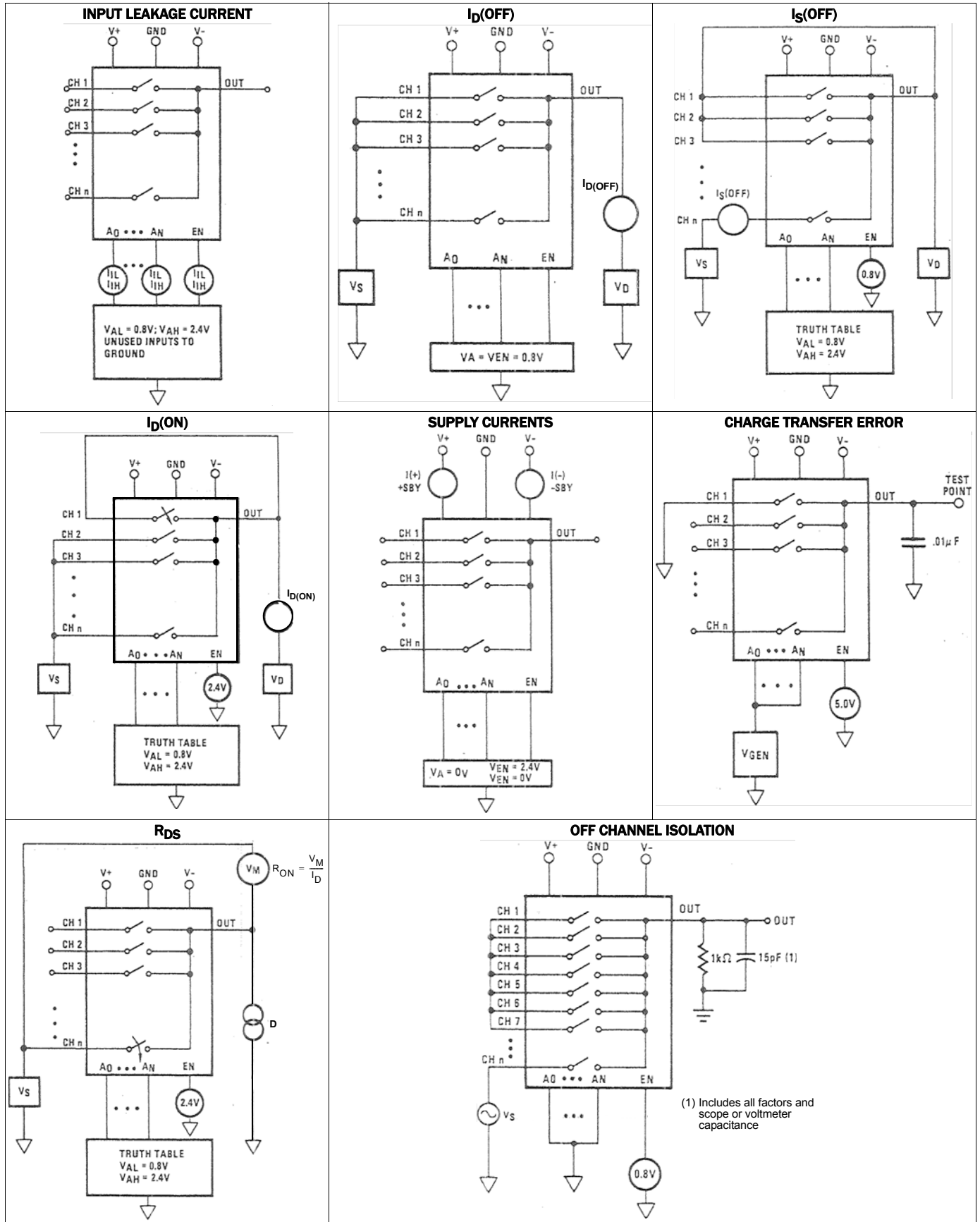
**TABLE 4. ELECTRICAL TEST REQUIREMENTS**

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (See Tables 1, 2, 3)
Interim Electrical Parameters (Pre Burn-in)	1
Final Electrical Test Parameters	1 (Note 4), 2, 3, 9, 10, 11
Group A Test Requirements	1, 2, 3, 9, 10, 11
Groups C & D Endpoints	1

NOTE:

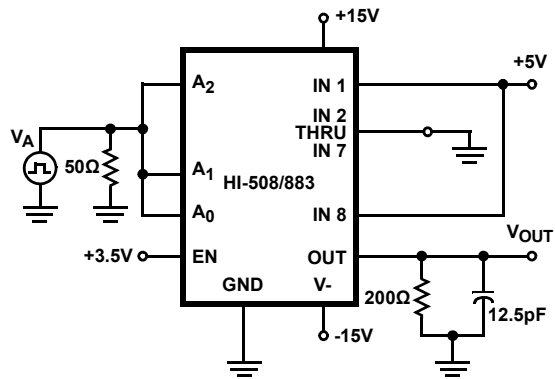
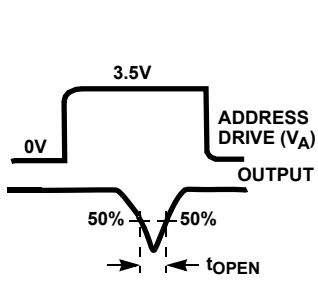
4. PDA applies to Subgroup 1 only. No other subgroups are included in PDA.

# Test Circuits

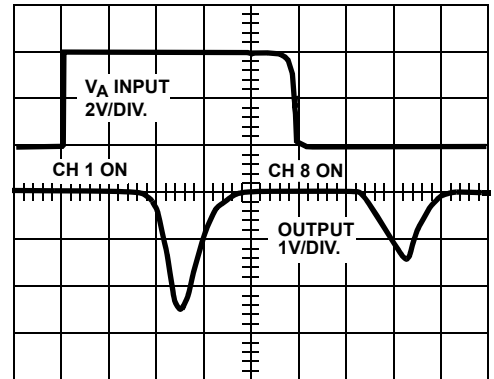


# Switching Waveforms

BREAK-BEFORE-MAKE DELAY ( $t_{OPEN}$ )

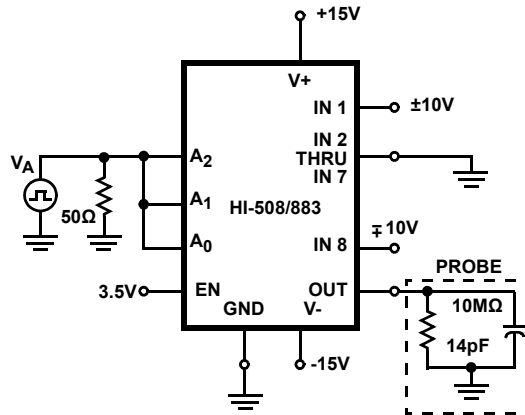
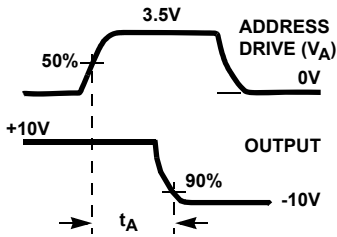


BREAK-BEFORE-MAKE DELAY ( $t_{OPEN}$ )

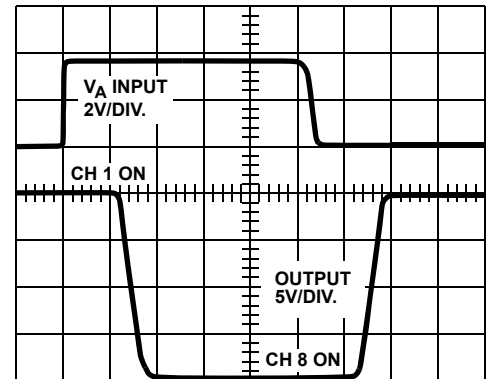


100ns/DIV.

ACCESS TIME vs LOGIC LEVEL (HIGH)

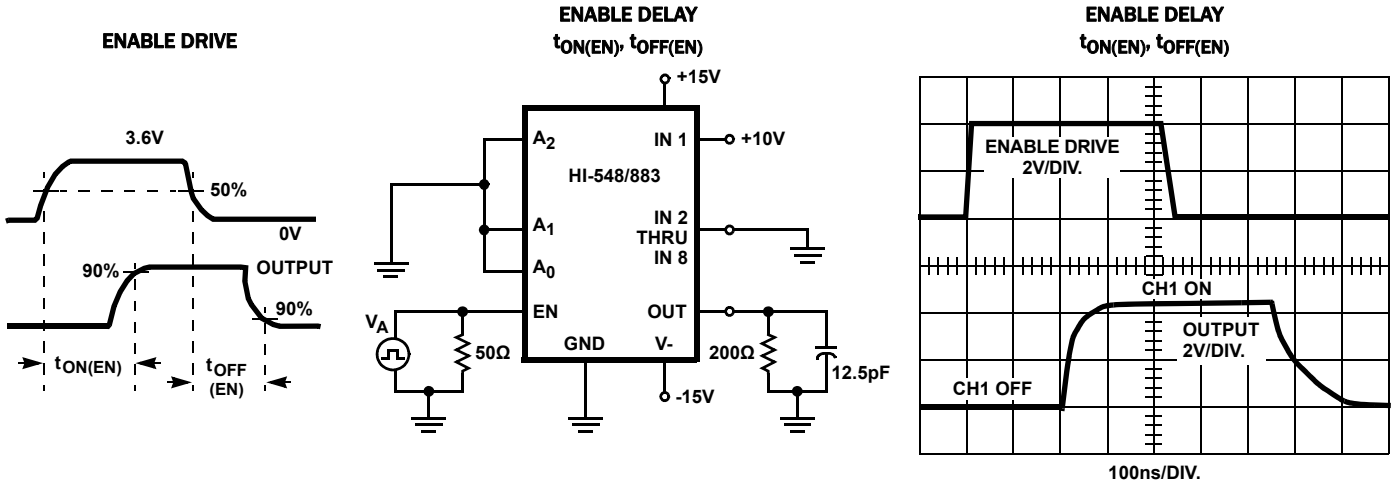


ACCESS TIME



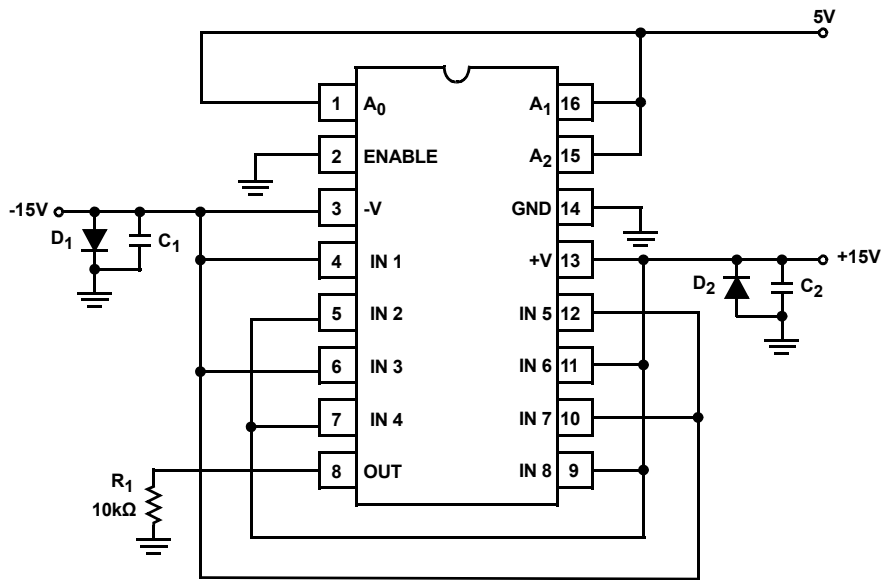
200ns/DIV.

# Switching Waveforms



# Burn-In Circuit

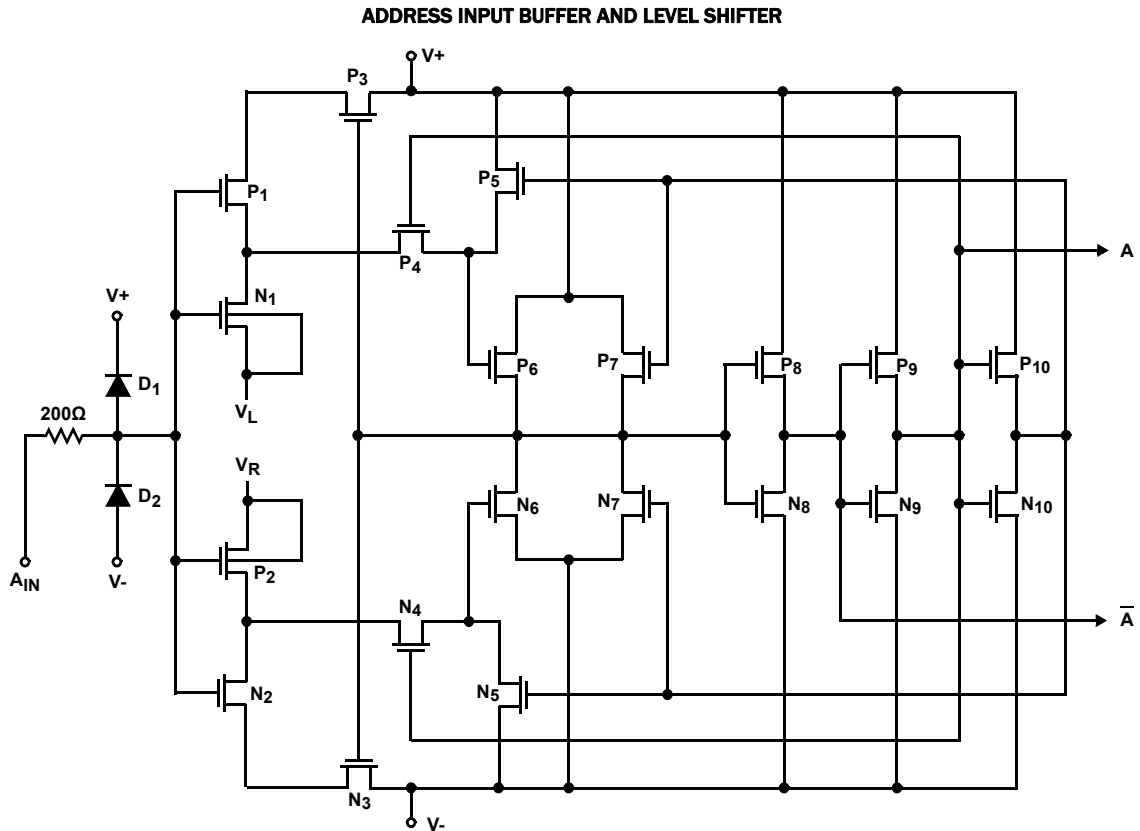
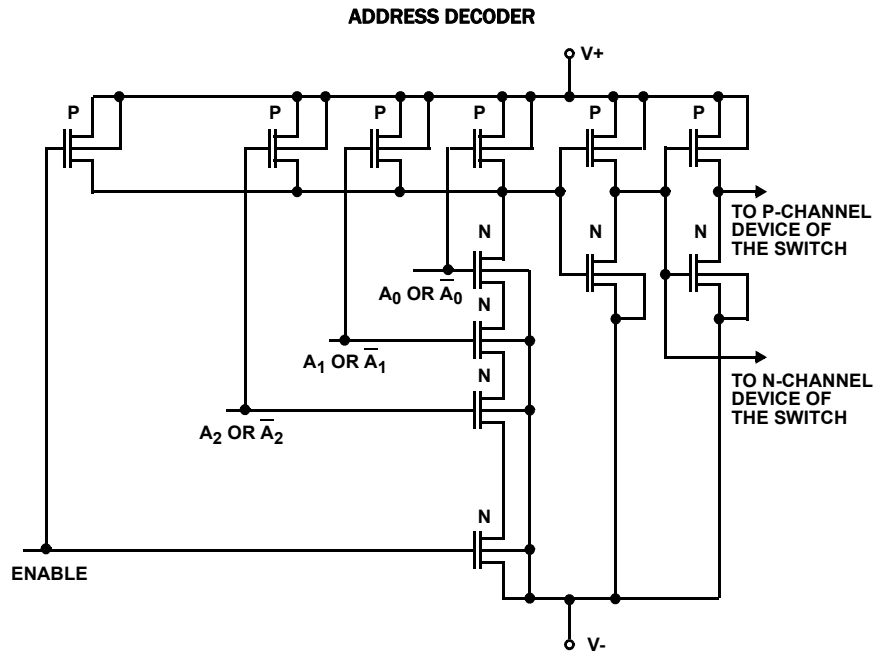
HI-508/883 CERDIP



**NOTES:**

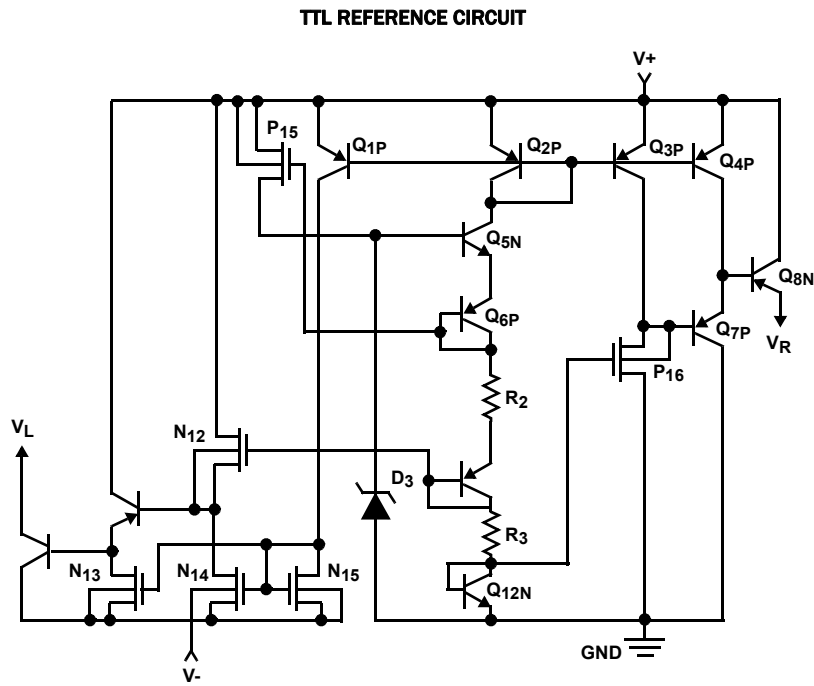
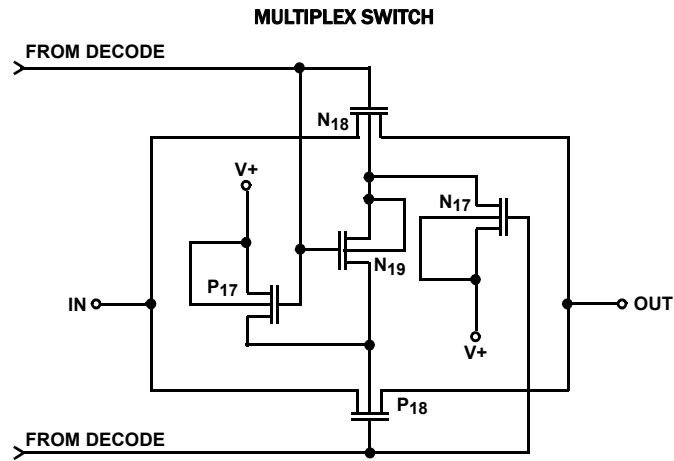
- R<sub>1</sub> = 10kΩ ± 5% 1/2W or 1/4W (per socket)
- C<sub>1</sub>, C<sub>2</sub> = 0.01μF (per socket) or 0.1μF (per row)
- D<sub>1</sub>, D<sub>2</sub> = 1N4002 (or equivalent) (per board)

# Schematic Diagrams



All N-Channel bodies to V-, all P-Channel bodies to V+, unless otherwise indicated.

**Schematic Diagrams (Continued)**





# Die Characteristics

## DIE DIMENSIONS:

81.9mils x 90.2mils x 19mils

## METALLIZATION:

Type: Al

Thickness:  $16\text{k}\text{\AA} \pm 2\text{k}\text{\AA}$

## GLASSIVATION:

Type: Nitride

Thickness:  $7\text{k}\text{\AA} \pm 0.7\text{k}\text{\AA}$

## WORST CASE CURRENT DENSITY:

$1.4 \times 10^5 \text{ A/cm}^2$

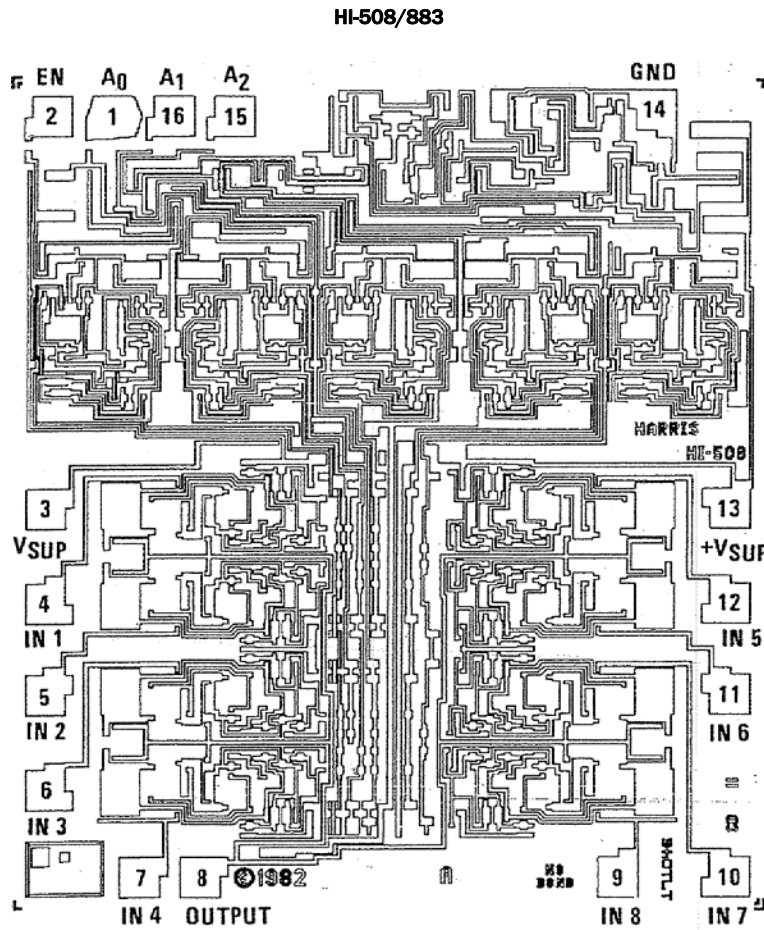
## TRANSISTOR COUNT:

243

## PROCESS:

CMOS-DI

# Metallization Mask Layout



**Design Information** The information contained in this section has been developed through characterization and is for use as application and design information only. No guarantee is implied.

### Typical Performance Curves

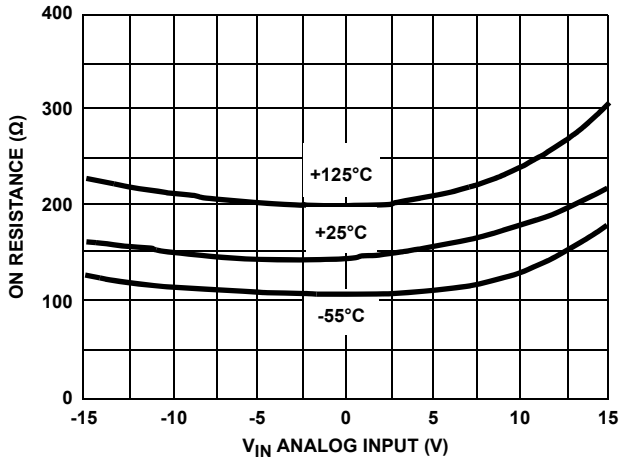


FIGURE 1. ON RESISTANCE vs ANALOG INPUT VOLTAGE, TEMPERATURE

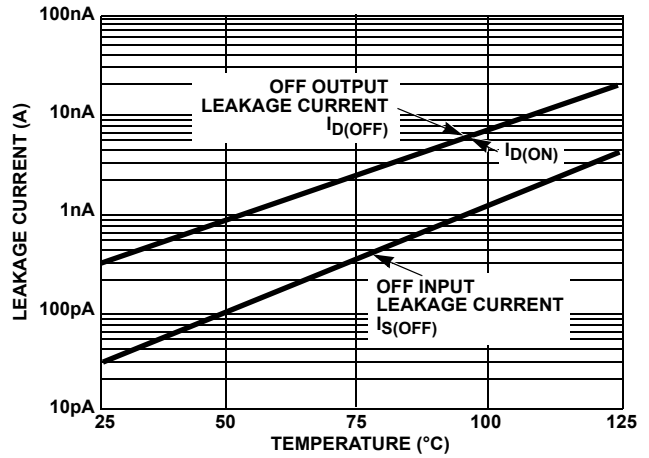


FIGURE 2. LEAKAGE CURRENT vs TEMPERATURE

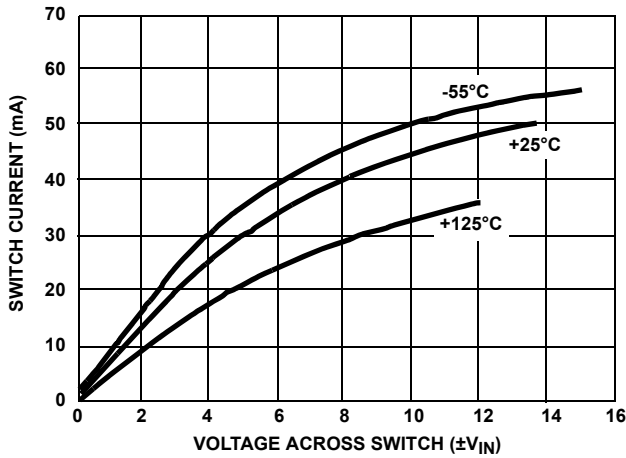


FIGURE 3. ON CHANNEL CURRENT vs VOLTAGE

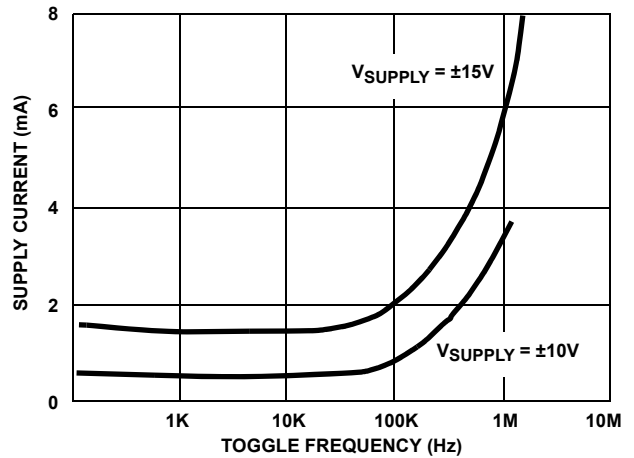
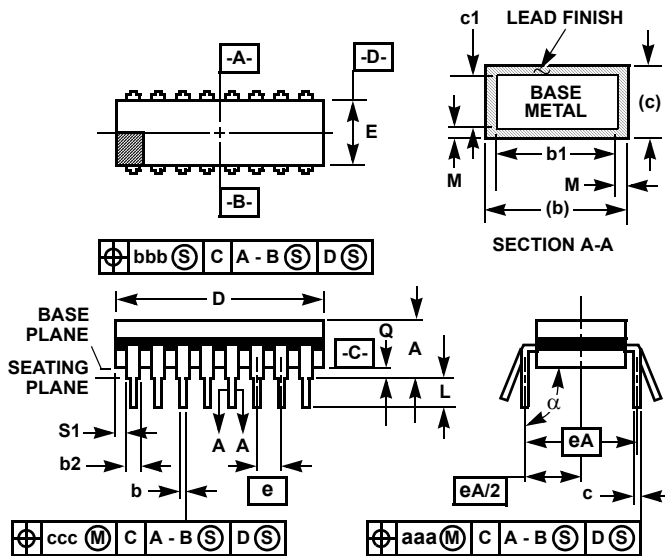


FIGURE 4A. SUPPLY CURRENT vs TOGGLE FREQUENCY

**Ceramic Dual-In-Line Frit Seal Packages (CERDIP)**



**F16.3 MIL-STD-1835 GDIP1-T16 (D-2, CONFIGURATION A)  
16 LEAD CERAMIC DUAL-IN-LINE FRIT SEAL PACKAGE**

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	-	0.200	-	5.08	-
b	0.014	0.026	0.36	0.66	2
b1	0.014	0.023	0.36	0.58	3
b2	0.045	0.065	1.14	1.65	-
b3	0.023	0.045	0.58	1.14	4
c	0.008	0.018	0.20	0.46	2
c1	0.008	0.015	0.20	0.38	3
D	-	0.840	-	21.34	5
E	0.220	0.310	5.59	7.87	5
e	0.100 BSC		2.54 BSC		-
eA	0.300 BSC		7.62 BSC		-
eA/2	0.150 BSC		3.81 BSC		-
L	0.125	0.200	3.18	5.08	-
Q	0.015	0.060	0.38	1.52	6
S1	0.005	-	0.13	-	7
alpha	90°	105°	90°	105°	-
aaa	-	0.015	-	0.38	-
bbb	-	0.030	-	0.76	-
ccc	-	0.010	-	0.25	-
M	-	0.0015	-	0.038	2, 3
N	16		16		8

**NOTES:**

1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark.
2. The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
3. Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness.
4. Corner leads (1, N, N/2, and N/2+1) may be configured with a partial lead paddle. For this configuration dimension b3 replaces dimension b2.
5. This dimension allows for off-center lid, meniscus, and glass overrun.
6. Dimension Q shall be measured from the seating plane to the base plane.
7. Measure dimension S1 at all four corners.
8. N is the maximum number of terminal positions.
9. Dimensioning and tolerancing per ANSI Y14.5M - 1982.
10. Controlling dimension: INCH.

Rev. 0 4/94

© Copyright Intersil Americas LLC 2012. All Rights Reserved.

All trademarks and registered trademarks are the property of their respective owners.

For additional products, see [www.intersil.com/en/products.html](http://www.intersil.com/en/products.html)

Intersil products are manufactured, assembled and tested utilizing ISO9001 quality systems as noted in the quality certifications found at [www.intersil.com/en/support/qualandreliability.html](http://www.intersil.com/en/support/qualandreliability.html)

*Intersil products are sold by description only. Intersil may modify the circuit design and/or specifications of products at any time without notice, provided that such modification does not, in Intersil's sole judgment, affect the form, fit or function of the product. Accordingly, the reader is cautioned to verify that datasheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.*

For information regarding Intersil Corporation and its products, see [www.intersil.com](http://www.intersil.com)